

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. SEPP21.001C	APPLICATION NO. 10/678,768
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT TOIS et al.	
		FILING DATE October 2, 2003	GROUP 1765

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
M	1.	5,480,818	01/02/96	Matsumoto et al.	437	40	02/09/93
M	2.	6,006,763	12/28/99	Mori et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
M	3.	JP 3286531 A2	12.17.91	Japan Abstract				
M	4.	JP 60065712 A2	04.15.85	Japan Abstract				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)							
M	5	Klaus, J. W. et al., "Atomic Layer Deposition of SiO ₂ Using Catalyzed and Uncatalyzed Self-Limiting Surface Reactions," <i>Surface Review and Letters</i> , Vol. 6, Nos. 3 & 4, pp. 435-448 (1999).						
	6	Niinistö, L. et al., "Synthesis of oxide thin films and overlayers by atomic layer epitaxy for advanced applications," <i>Materials Science and Engineering</i> , B41, pp. 23-29 (1996).						
	7	Wise, M. L. et al., "Diethyldioxysilane as a New Precursor for SiO ₂ Growth on Silicon," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 334, pp. 37-43 (1994).						
	8	Yamaguchi, Kei-ichi et al., "Atomic-layer chemical-vapor-deposition of silicon dioxide films with an extremely low hydrogen content," <i>Appl. Surf. Science</i> , 130-132; pp. 202-207 (1998)						
	9	George, S.M., et al., "Surface Chemistry for Atomic Layer Growth," <i>J. Phys. Chem.</i> , 100:13121-13131 (1996)						
	10	George, S.M. et al., "Atomic layer controlled deposition of SiO ₂ and Al ₂ O ₃ using ABAB... binary reaction sequence chemistry," <i>Appl. Surf. Science</i> , 82/83:460-487 (1994)						
	11	Jeon, H., "A Study on the Characteristics of TIN Thin Film Deposited by Atomic Layer Chemical Vapor Deposition Method," <i>AVS 46th International Symposium</i> , Seattle, WA, abstract TF-MoP17 (1999)						
	12	Jeon, H., et al., "A Study on the Characteristics of TIN Thin Film Deposited by Atomic Layer Chemical Vapor Deposition Method," <i>J. Vac. Sci. Technol. A</i> , 18(4), 1595-1598 (2000)						
	13	Klaus, J.W., et al., "Atomically controlled growth of tungsten and tungsten nitride using sequential surface reactions," <i>Appl. Surf. Science</i> 162-163; 479-471 (2000)						
	14	Klaus, J.W., et al., "Atomic layer deposition of tungsten nitride films using sequential surface reactions," <i>Journal of the Electrochemical Soc.</i> , 147 (3):1175-1181 (2000)						
	15	Klaus, J.W. et al., "Atomic layer deposition of tungsten using sequential surface chemistry with a sacrificial stripping reaction," <i>Thin Solid Films</i> , 360:145-153 (2000)						
	16	Klaus, J.W., et al., "Atomic layer deposition of tungsten and tungsten nitride using sequential surface reactions," <i>AVS 46th International Symposium</i> , Seattle, WA, abstract TF-TuM6 (1999)						
M	17	Riihelä, D. et al., "Introducing atomic layer epitaxy for the deposition of optical thin films," <i>Thin Solid Films</i> , Vol. 289, pp. 250-255 (1996).						

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EXAMINER	<i>Mori</i>	DATE CONSIDERED	9/25/2004
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.			